

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|--|------------------|---------|------------------|
| L2 | 2 | ("NAND") and (source adj slot) and (drain adj contact) and (source adj select adj (gate or electrode)) and (drain adj select adj (gate or electrode)) and ((single or one) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:01 |
| L3 | 2 | (((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET")) and (source adj slot) and (drain adj contact) and (source adj select adj (gate or electrode)) and (drain adj select adj (gate or electrode)) and ((single or one) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:04 |
| L4 | 271 | (((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET")) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single or one) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:05 |
| L5 | 144 | (((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET")) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:22 |
| L6 | 144 | (((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET")) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:06 |

EAST Search History

| | | | | | | |
|-----|------|--|--|----|----|------------------|
| L7 | 0 | (((((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) with ((single or one) adj mask\$4)) and ((single) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:23 |
| L8 | 0 | (((((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) near ((single or one) adj mask\$4)) and ((single) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:23 |
| L9 | 2 | (((((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) same ((single or one) adj mask\$4)) and ((single) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:24 |
| L10 | 144 | (((((memory adj array) or ("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) and ((single or one) adj mask\$4)) and ((single) adj mask\$4) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 10:25 |
| S1 | 1863 | NAND with source with drain | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/27 12:24 |

EAST Search History

| | | | | | | |
|-----|------|---|--|----|-----|------------------|
| S2 | 1359 | (NAND with source with drain) and semiconductor and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/19 13:25 |
| S3 | 31 | (NAND with source with drain) and semiconductor and slot and contact and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:47 |
| S5 | 4 | (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:19 |
| S6 | 159 | ((memory adj cell) with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/19 13:24 |
| S7 | 4 | ("20020149081") or ("6115287") or ("6411548") or ("5780338"). PN. | US-PGPUB; USPAT | OR | OFF | 2005/03/24 14:00 |
| S8 | 0 | ((memory adj cell) with source with drain) with (single adj mask\$6)) and semiconductor and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/19 13:24 |
| S9 | 0 | (NAND with source with drain with (single adj mask\$6)) and semiconductor and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/19 13:25 |
| S10 | 0 | (NAND with source with drain with (single adj mask\$6)) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/19 13:25 |

EAST Search History

| | | | | | | |
|-----|------|---|---|----|-----|------------------|
| S11 | 2226 | (438/586).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/27 10:19 |
| S12 | 0 | 438/586.ccls. and (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/27 12:37 |
| S13 | 1 | "438"/\$.ccls. and (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:20 |
| S14 | 4 | "257"/\$.ccls. and (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:24 |
| S15 | 0 | ("257"/\$.ccls. with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:25 |
| S16 | 0 | ("438"/\$.ccls. with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:25 |
| S17 | 0 | (("438"/\$.ccls.) with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:25 |
| S18 | 0 | (("257"/\$.ccls.) with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:26 |

EAST Search History

| | | | | | | |
|-----|------|--|---|----|-----|------------------|
| S19 | 0 | (("257"/\$.ccls.) with source with drain) and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/04/27 10:26 |
| S20 | 0 | (("438"/\$.ccls.) with source with drain) and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/19 06:45 |
| S21 | 0 | (("438"/\$.ccls.) with source with drain) and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/19 06:45 |
| S22 | 6 | ((NAND) with source with drain) and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/19 06:55 |
| S23 | 6 | (("20020149081") or ("6115287") or ("6411548")).PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/09/19 06:55 |
| S24 | 2218 | ("NAND") with source with drain | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/27 12:25 |
| S25 | 40 | ("NAND") with source with drain with mask | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/27 12:28 |
| S26 | 3 | ("NAND") with source with drain with (single adj mask) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/27 12:25 |

EAST Search History

| | | | | | | |
|-----|----|---|---|----|----|------------------|
| S27 | 36 | (("NAND") with source with drain with mask) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/27 12:28 |
| S28 | 1 | 438/586.ccls and (NAND with source with drain) and semiconductor and (single adj mask\$6) and @ad<="20031023" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/27 12:38 |